

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
	G05115A	0	1 of 1

TYPE:6PT18B6P3T * *

CHIP SIZE	0.80 * 0.80mm
WAFER SIZE	6inch
POSSIBLE DIE PER WAFER	23,580pcs

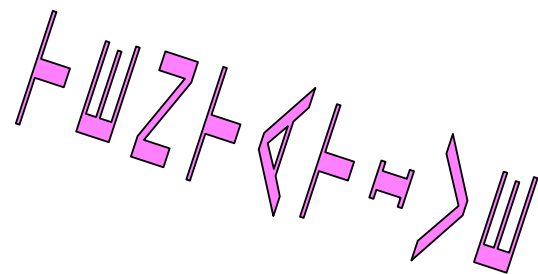
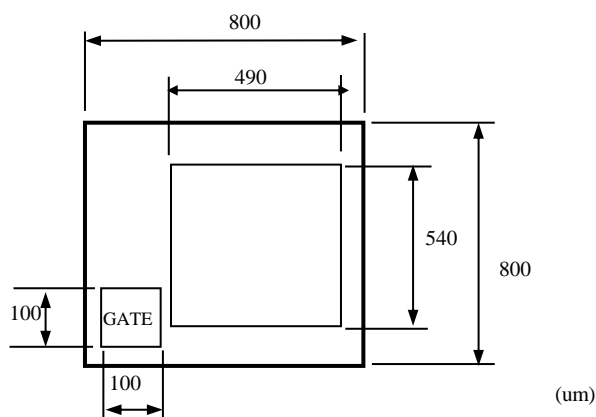
Maximum Ratings (Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	-50	V
Gate-source voltage	VGSS	±20	V

WAFER PROBING SPEC (Ta=25°C)

TEST NO.	MODE	LIMIT			UNIT	CONDITION
		MIN	Typ	MAX		
1	IGSS			±8	uA	VGS=±20.0V VDS=0V
2	IDSS			500	nA	VDS=-52.0V VGS=0V
3	BVDSS	-52			V	ID=-100uA
4	VTH	-1.05		-1.95	V	ID=-250uA
5	Ron 1		0.25	0.45	Ω	ID=-1.0A VGS=-10V
6	Ron 2		0.35	0.58	Ω	ID=-1.0A VGS=-4.0V
7	VSD	-0.5			V	IS=-2.0A

※ Built-inZD betweenGate and Source. ESD Protected : 2000V



NOTE: